

N-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A) ^a			
60	0.0025 at V _{GS} = 10 V	150			
	0.0051 at V _{GS} = 4.5 V	75			

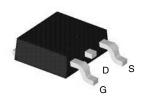
FEATURES

- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested

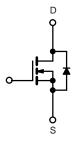


COMPLIANT

TO-252 Pin Configuration



Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)						
Parameter	Symbol	Limit	Unit			
Gate-Source Voltage	V_{GS}	± 20	V			
Continuous Drain Current (T _{.1} = 175 °C) ^b	T _C = 25 °C	L	150			
Continuous Drain Current (1 _J = 175 °C) ²	T _C = 100 °C	l _D	85 ^a			
Pulsed Drain Current	I _{DM}	600	А			
Continuous Source Current (Diode Conduction)	I _S	120 ^a				
Avalanche Current	I _{AS}	130				
Single Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E _{AS}	289	mJ		
Maximum Power Dissipation	T _C = 25 °C	P _D	205	W		
Maximum Fower Dissipation	T _A = 25 °C	' D	5.6 ^b			
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 175	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Mariana lungtion to Ambienta	t ≤ 10 sec	Р	9	15	°C/W	
Maximum Junction-to-Ambient ^a	Steady State	R_{thJA}	15	45		
Maximum Junction-to-Case	·	R _{thJC}	0.95	1.5		

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- $c.\ t \leq 10\ s.$





SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
Parameter	Symbol	Test Conditions		Typ. ^a	Max.	Unit	
Static					l l		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	60			V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1	-	3		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V _{DS} = 48 V, V _{GS} = 0 V			1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 48 V, V _{GS} = 0 V, T _J = 125 °C			50	50 μA 250	
		V _{DS} = 48 V, V _{GS} = 0 V, T _J = 175 °C			250		
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	150			Α	
		V _{GS} = 10 V, I _D = 20 A		0.0025	0.0033		
5 1 6 6 6 1 5 1 1 b	Ь	V _{GS} = 10 V, I _D =20 A, T _J = 125 °C		0.0032	0.0040	Ω	
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D =15 A, T _J = 175 °C		0.0039	0.0048		
		V _{GS} = 4.5 V, I _D = 15 A		0.0051	0.0062		
Forward Transconductance ^b	9 _{fs}	$V_{DS} = 48 \text{ V}, I_{D} = 20 \text{ A}$		166		S	
Dynamic	•			•	•		
Input Capacitance	C _{iss}			10120		pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 48 \text{ V}, f = 1 \text{ MHz}$		1588			
Reverse Transfer Capacitance	C _{rss}			157			
Total Gate Charge ^c	Q_g			75	89	nC	
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = 48 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 20 \text{ A}$		15			
Gate-Drain Charge ^c	Q_{gd}			19			
Turn-On Delay Time ^c	t _{d(on)}			18			
Rise Time ^c	t _r	$V_{DD} = 48 \text{ V}, R_{L} = 0.6 \Omega$		32		ns	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 20 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 2.5 \Omega$		66			
Fall Time ^c	t _f			13			
Source-Drain Diode Ratings and Cha	aracteristics (T _C = 25 °C)					
Pulsed Current	I _{SM}				600	Α	
Diode Forward Voltage	V _{SD}	$I_F = 20 \text{ A}, V_{GS} = 0 \text{ V}$			1.25	V	
Reverse Recovery Time	t _{rr}	I _F = 20 A, di/dt = 100 A/μs		73		ns	

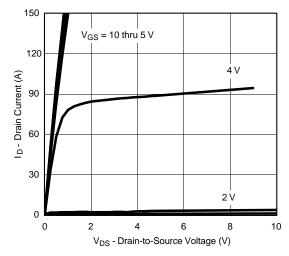
Notes:

- a. For design aid only; not subject to production testing.
- b. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- c. Independent of operating temperature.

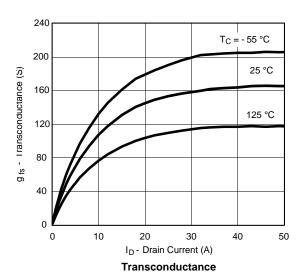
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



TYPICAL CHARACTERISTICS (25 °C unless noted)

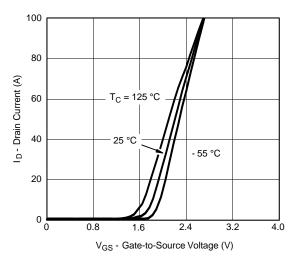


Output Characteristics

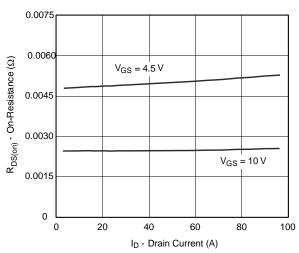


12000 10500 $\mathsf{C}_{\mathsf{iss}}$ 9000 C - Capacitance (pF) 7500 6000 4500 3000 Coss 1500 0 0 10

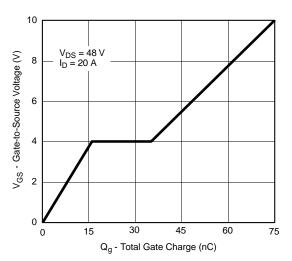
30 50 60 V_{DS} - Drain-to-Source Voltage (V) Capacitance



Transfer Characteristics



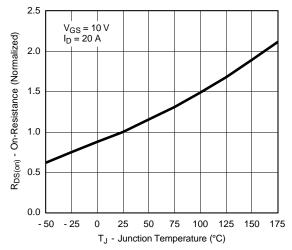
On-Resistance vs. Drain Current



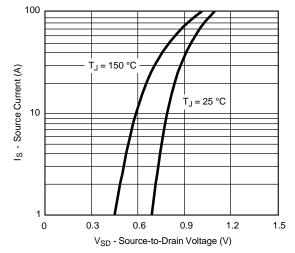
Gate Charge



TYPICAL CHARACTERISTICS (25 °C unless noted)



On-Resistance vs. Junction Temperature

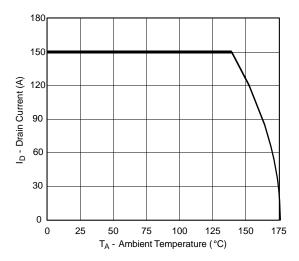


Source-Drain Diode Forward Voltage



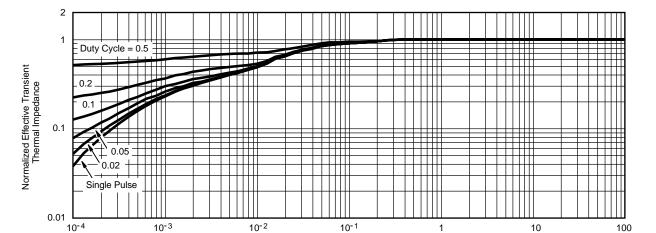


THERMAL RATINGS



1000 Limited by R_{DS(on)}* 100 10 µs 100 µs I_D - Drain Current (A) 10 1 ms 10 ms 100 ms DC T_C = 25 °C Single Pulse 0.1 0.01 L 0.1 100 $V_{DS} - Drain-to-Source \ Voltage \ (V) \\ ^*V_{GS} > minimum \ V_{GS} \ at \ which \ R_{DS(on)} \ is \ specified$ Safe Operating Area

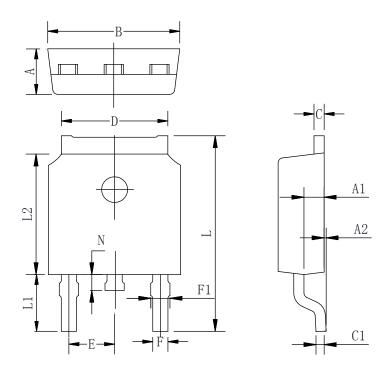
Maximum Drain Current vs. Ambient Temperature



Normalized Thermal Transient Impedance, Junction-to-Case

Square Wave Pulse Duration (s)

TO-252-2L PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Symbol	Min	Тур	Max	
A	2.10	2.30	2.50	
A1	0.88	1.01	1.16	
A2	0.00	0.15	0.28	
В	6.40	6.60	6.80	
С	0.42	0.50	0.63	
C1	0.42	0.50	0.63	
D	5.08	5.32	5.65	
Е	2.286 TYP			
F	0.63	0.76	0.89	
F1	0.64	0.86	1.08	
L	9.30	9.90	10.80	
L1	2.4	2.8	3.6	
L2	5.90	6.10	6.55	
N	0.57	0.80	1.05	

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